

BC846BMB

65 V, 100 mA NPN general-purpose transistor Rev. 1 — 15 May 2012

Product data sheet

Product profile

1.1 General description

NPN general-purpose transistor in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

1.3 Applications

- General-purpose switching and amplification
- Mobile applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	65	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	200	-	450	

2. Pinning information

Table 2. **Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	1 3	3
3	collector	2	1—
		Transparent	2
		top view	sym021



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3. Ordering information

Table 3. Ordering information

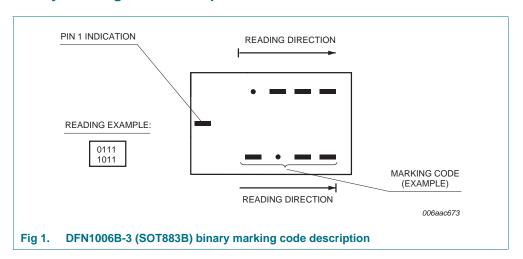
Type number	Package					
	Name	Description	Version			
BC846BMB	DFN1006B-3	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.37$ mm	SOT883B			

4. Marking

Table 4. Marking codes

Type number	Marking code
BC846BMB	0100 1011

4.1 Binary marking code description



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0, 1	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	80	V
V_{CEO}	collector-emitter voltage	open base	-	65	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

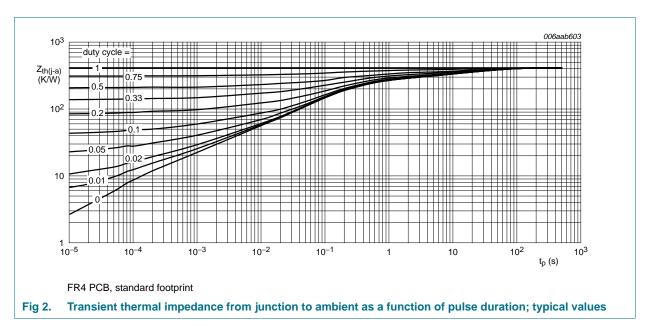
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

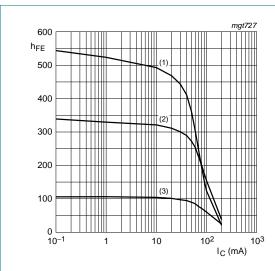
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base	$V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}$		-	-	15	nA
	cut-off current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{E} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$		200	-	450	
V_{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$		-	90	200	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[1]	-	200	400	mV
V_{BEsat}	at base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	[2]	-	760	-	mV
saturation voltage	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[2]	-	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	[3]	580	660	700	mV
		$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	[3]	-	-	770	mV
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	2	3	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz		-	11	-	pF
NF	noise figure	$I_C = 200 \mu A; V_{CE} = 5 V;$ $R_S = 2 k\Omega; f = 1 kHz;$ B = 200 Hz		-	2	10	dB

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] V_{BEsat} decreases by approximately 1.7 mV/K with increasing temperature.

^[3] V_{BE} decreases by approximately 2 mV/K with increasing temperature.

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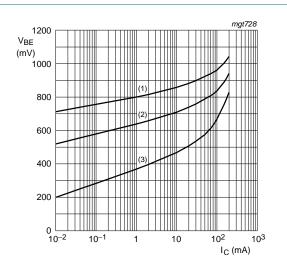


$$V_{CE} = 5 V$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



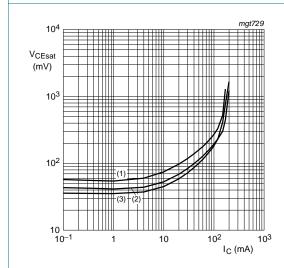
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. Base-emitter voltage as a function of collector current; typical values



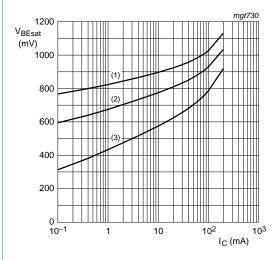
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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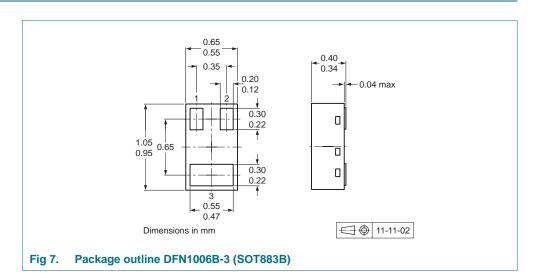
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8. Test information

9. Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

10. Package outline



11. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

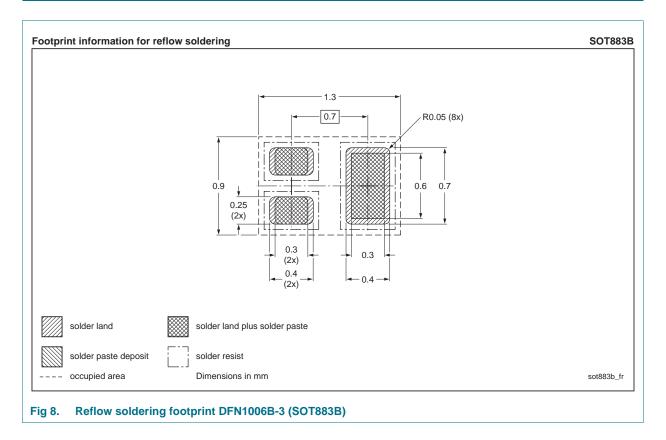
Type number	Package	Description	Packing quantity
			10000
BC846MBM	SOT883B	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see Section 15.

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12. Soldering



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13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846BMB v.1	20120515	Product data sheet	-	-

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14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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